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| SANYO | No.575D | 2SB764/2SD863 |
| | PNP/NPN Epitaxial Planar Silicon Transistors Voltage Regulator, Relay Lamp Driver Electrical Equipment Applications | |

(): 2SB764

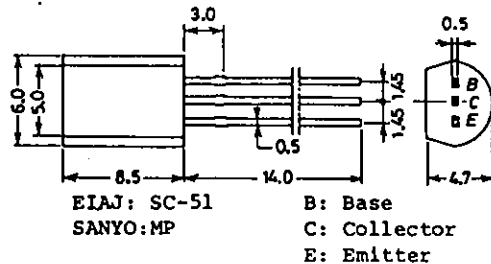
| Absolute Maximum Ratings at Ta=25°C | | | unit |
|-------------------------------------|------------------|-------------|------|
| Collector to Base Voltage | V _{CB0} | (-)60 | V |
| Collector to Emitter Voltage | V _{CE0} | (-)50 | V |
| Emitter to Base Voltage | V _{EB0} | (-)5 | V |
| Collector Current | I _C | (-)1 | A |
| Collector Current(Pulse) | I _{CP} | (-)2 | A |
| Collector Dissipation | P _C | 0.9 | W |
| Junction Temperature | T _J | 150 | °C |
| Storage Temperature | T _{stg} | -55 to +150 | °C |

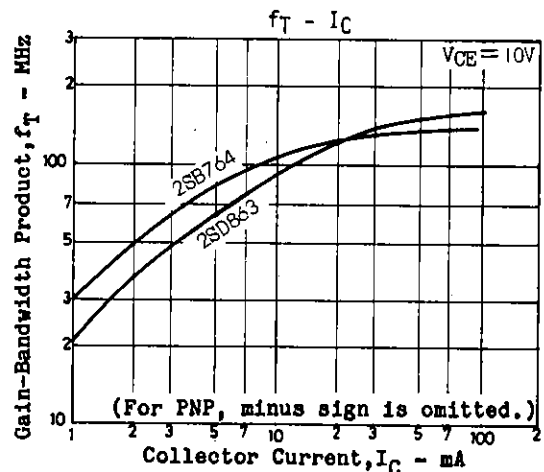
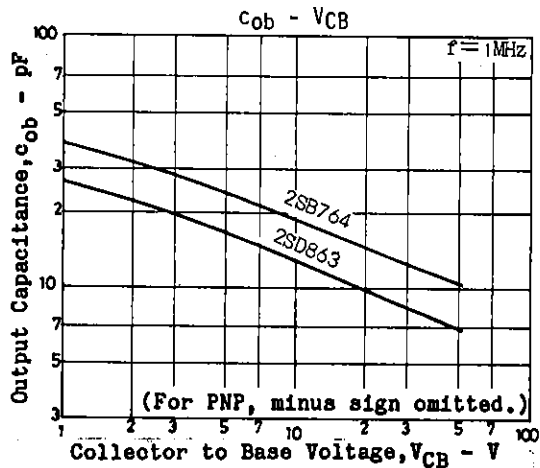
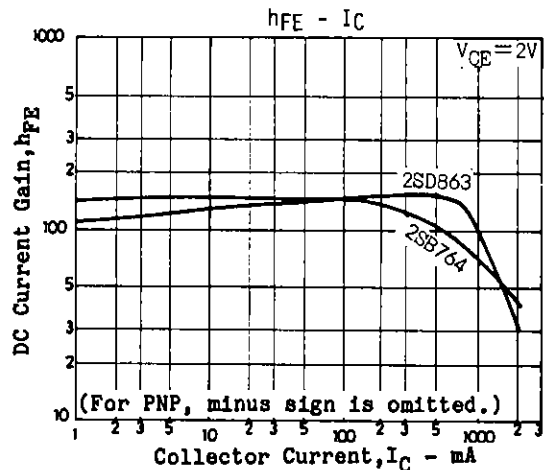
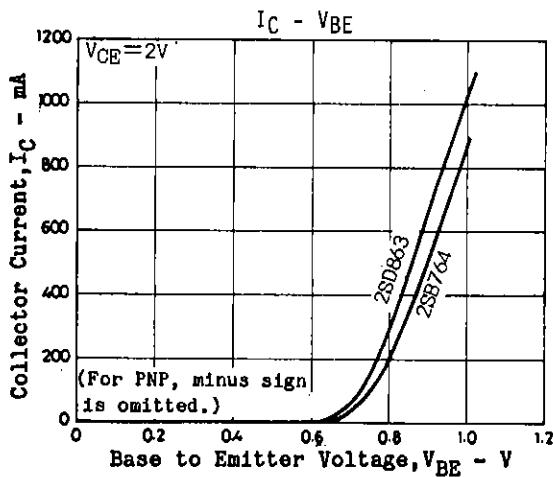
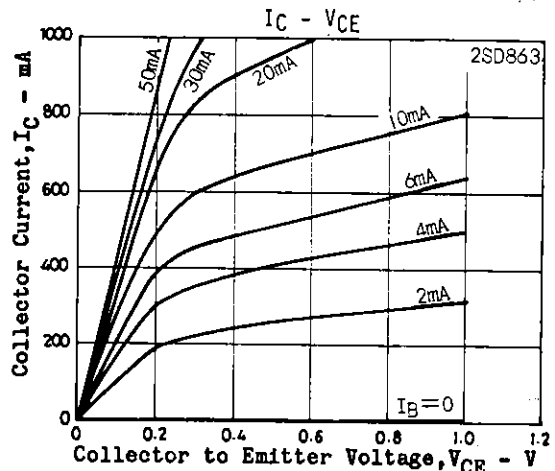
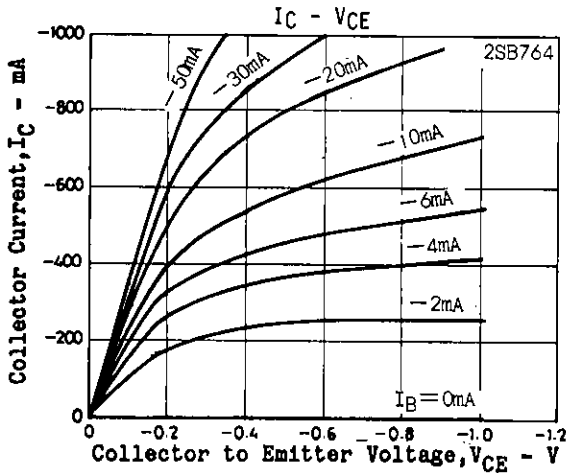
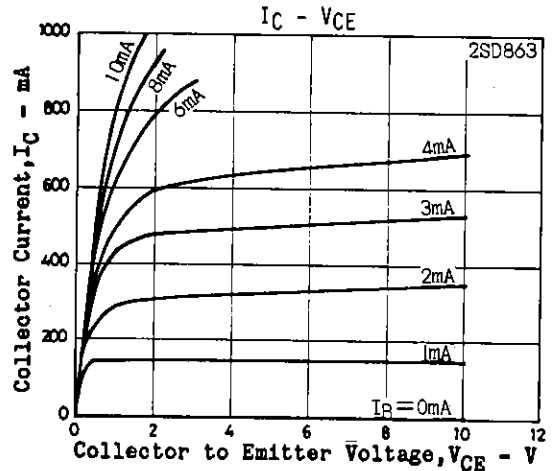
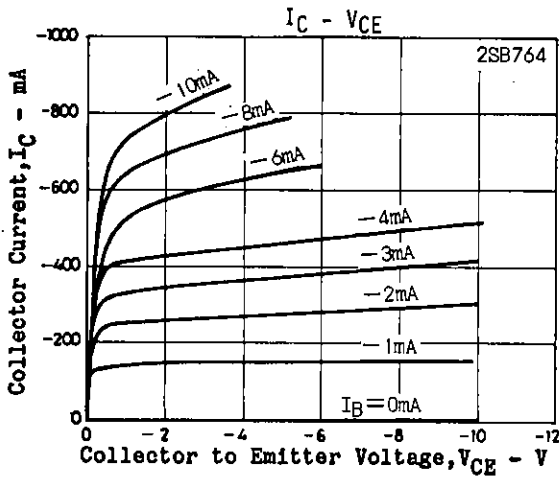
| Electrical Characteristics at Ta=25°C | | | min | typ | max | unit |
|---------------------------------------|----------------------|---|-------|---------------|------|------|
| Collector Cutoff Current | I _{CBO} | V _{CB} =(-)50V, I _E =0 | | | (-)1 | μA |
| Emitter Cutoff Current | I _{EBO} | V _{EB} =(-)4V, I _C =0 | | | (-)1 | μA |
| DC Current Gain | h _{FE} (1) | V _{CE} =(-)2V, I _C =(-)50mA | 60* | | 320* | |
| | | V _{CE} =(-)2V, I _C =(-)1A | 30 | | | |
| Gain-Bandwidth Product | f _T | V _{CE} =(-)10V, I _C =(-)50mA | | 150 | | MHz |
| Output Capacitance | c _{ob} | V _{CE} =(-)10V, f=1MHz | | (20) | | pF |
| | | | | 12 | | pF |
| C-E Saturation Voltage | V _{CE(sat)} | I _C =(-)500mA, I _B =(-)50mA | | (-0.2)(-0.7) | | V |
| | | | | 0.15 | 0.5 | V |
| B-E Saturation Voltage | V _{BE(sat)} | I _C =(-)500mA, I _B =(-)50mA | | (-)0.85(-)1.2 | | V |
| C-B Breakdown Voltage | V _{(BR)CBO} | I _C =(-)10μA, I _E =0 | (-)60 | | | V |
| C-E Breakdown Voltage | V _{(BR)CEO} | I _C =(-)1mA, R _{BE} =∞ | (-)50 | | | V |
| E-B Breakdown Voltage | V _{(BR)EBO} | I _E =(-)10μA, I _C =0 | (-)5 | | | V |

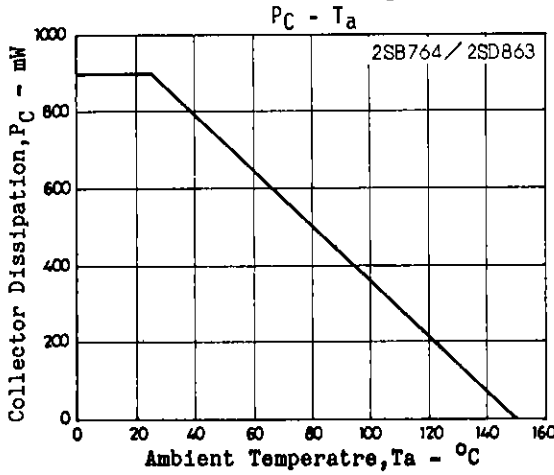
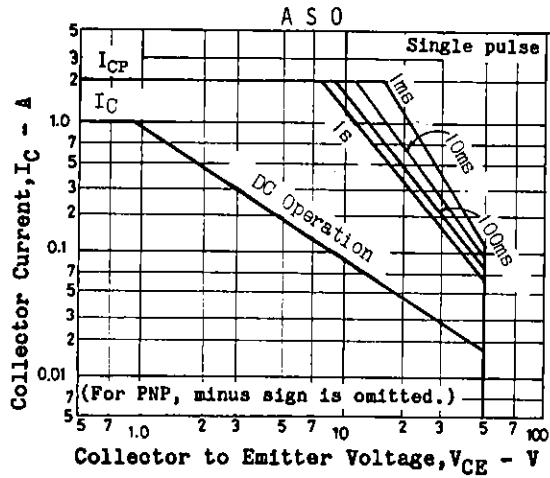
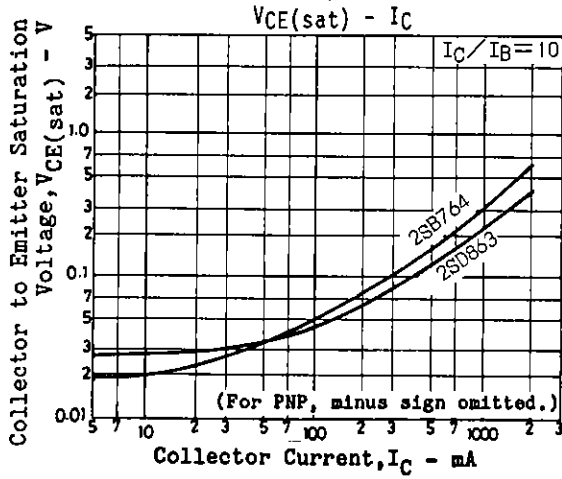
* The 2SB764/2SD863 are classified by 50mA h_{FE} as follows.

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|----|---|-----|-----|---|-----|-----|---|-----|
| 60 | D | 120 | 100 | E | 200 | 160 | F | 320 |
|----|---|-----|-----|---|-----|-----|---|-----|

Package Dimensions 2006A
(unit: mm)







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